

1. Material Substrate GaAlAs (P Type) Removed
Epitaxial Layer GaAlAs (N/P Type)

2. Electrode N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.1		V	IF=10uA
	$V_{F(2)}$		1.8	2	V	IF=100mA
Reverse Voltage	V_R	5			V	IR=10uA
Power	P_O	10	12		mW	IF=100mA
Wavelength	λ_P		888		nm	IF=50mA
	$\Delta\lambda$		45		nm	IF=50mA
Rise Time	T_r		25		ns	Tp=400ns, Duty=50%, IFP=50mA
Fall Time	T_f		20		ns	

※ Note : Power is measured by Sorter E/T system with bare chip.

- 4. Mechanical Data**
- (a) Emission Area ----- 12.8mil x 12.8mil
 - (b) Bottom Area ----- 13.8mil x 13.8mil
 - (c) Bonding Pad ----- 130um
 - (d) Chip Thickness ----- 7mil
 - (e) Junction Height ----- 4.6mil

